



N-CHANNEL MOSFET

Qualified per MIL-PRF-19500/557

Qualified Levels:
JAN, JANTX, JANTXV
and JANS*

DESCRIPTION

This family of switching transistors is military qualified up to the JANTXV level for high-reliability applications. The 2N6798 part number is also qualified to the JANS level. These devices are also available in a low profile U-18 LCC surface mount package. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N6796, 2N6798, 2N6800 and 2N6802 number series.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/557.
*JANS qualification is available on 2N6798 only.
(See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

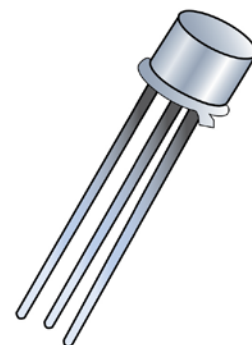
APPLICATIONS / BENEFITS

- Lightweight top-hat design with flexible terminals offers a variety of mounting flexibility.
- Military and other high-reliability applications.

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise stated

Parameters / Test Conditions	Symbol	Value	Unit
Operating & Storage Junction Temperature Range	T_J & T_{stg}	-55 to +150	$^\circ\text{C}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	5.0	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = +25^\circ\text{C}$ @ $T_C = +25^\circ\text{C}$ ⁽¹⁾	P_T	0.8 25	W
Drain-Source Voltage, dc 2N6796 2N6798 2N6800 2N6802	V_{DS}	100 200 400 500	V
Gate-Source Voltage, dc	V_{GS}	± 20	V
Drain Current, dc @ $T_C = +25^\circ\text{C}$ ⁽²⁾ 2N6796 2N6798 2N6800 2N6802	I_{D1}	8.0 5.5 3.0 2.5	A
Drain Current, dc @ $T_C = +100^\circ\text{C}$ ⁽²⁾ 2N6796 2N6798 2N6800 2N6802	I_{D2}	5.0 3.5 2.0 1.5	A
Off-State Current (Peak Total Value) ⁽³⁾ 2N6796 2N6798 2N6800 2N6802	I_{DM}	32 22 14 11	A (pk)
Source Current 2N6796 2N6798 2N6800 2N6802	I_S	8.0 5.5 3.0 2.5	A

See notes on next page.



**TO-205AF (TO-39)
Package**

Also available in:

U-18 LCC package

(surface mount)
 2N6796U, 2N6798U,
2N6800U & 2N6802U

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
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Website:

www.microsemi.com

- Notes:**
1. Derate linearly 0.2 W/°C for $T_C > +25\text{ }^{\circ}\text{C}$.
 2. The following formula derives the maximum theoretical I_D limit. I_D is also limited by package and internal wires and may be limited due to pin diameter.

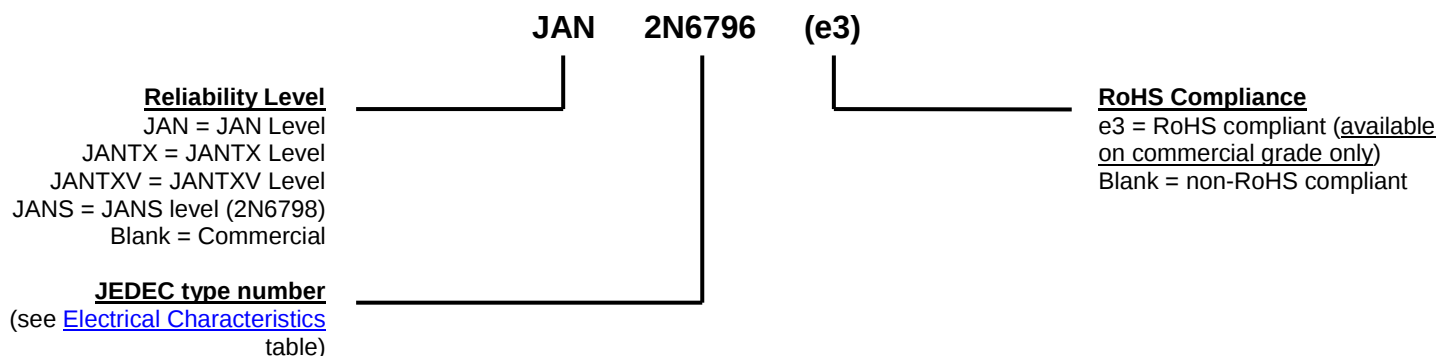
$$I_D = \sqrt{\frac{T_J(\text{max}) - T_C}{R_{\theta JC} \times R_{DS(on)} @ T_J(\text{max})}}$$

3. $I_{DM} = 4 \times I_{D1}$ as calculated in note 2.

MECHANICAL and PACKAGING

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Tin/lead solder dip nickel plate or RoHS compliant pure tin plate (commercial grade only).
- MARKING: Part number, date code, manufacturer's ID.
- WEIGHT: Approximately 1.064 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
di/dt	Rate of change of diode current while in reverse-recovery mode, recorded as maximum value.
I_F	Forward current
R_G	Gate drive impedance
V_{DD}	Drain supply voltage
V_{DS}	Drain source voltage, dc
V_{GS}	Gate source voltage, dc

ELECTRICAL CHARACTERISTICS @ $T_A = +25^\circ\text{C}$, unless otherwise noted

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	2N6796 2N6798 2N6800 2N6802	$V_{(BR)DSS}$	100 200 400 500		V
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = +125^\circ\text{C}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = -55^\circ\text{C}$		$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	V
Gate Current $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}, T_J = +125^\circ\text{C}$		I_{GSS1} I_{GSS2}		± 100 ± 200	nA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}$	2N6796 2N6798 2N6800 2N6802	I_{DSS1}		25	μA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}, T_J = +125^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}, T_J = +125^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}, T_J = +125^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}, T_J = +125^\circ\text{C}$	2N6796 2N6798 2N6800 2N6802	I_{DSS2}		0.25	mA
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 5.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 3.5\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 2.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 1.5\text{ A pulsed}$	2N6796 2N6798 2N6800 2N6802	$r_{DS(on)1}$		0.18 0.40 1.00 1.50	Ω
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 8.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 5.5\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 3.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 2.5\text{ A pulsed}$	2N6796 2N6798 2N6800 2N6802	$r_{DS(on)2}$		0.195 0.420 1.100 1.600	Ω
Static Drain-Source On-State Resistance $T_J = +125^\circ\text{C}$ $V_{GS} = 10\text{ V}, I_D = 5.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 3.5\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 2.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 1.5\text{ A pulsed}$	2N6796 2N6798 2N6800 2N6802	$r_{DS(on)3}$		0.35 0.75 2.40 3.50	Ω
Diode Forward Voltage $V_{GS} = 0\text{ V}, I_D = 8.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 5.5\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 3.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 2.5\text{ A pulsed}$	2N6796 2N6798 2N6800 2N6802	V_{SD}		1.5 1.4 1.4 1.4	V

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^{\circ}\text{C}$, unless otherwise noted (continued)
DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Gate Charge:				
On-State Gate Charge	$Q_{g(on)}$			
$V_{GS} = 10\text{ V}, I_D = 8.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6796			28.51	nC
$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6798			42.07	
$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6800			34.75	
$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6802			33.00	
Gate to Source Charge	Q_{gs}			
$V_{GS} = 10\text{ V}, I_D = 8.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6796			6.34	nC
$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6798			5.29	
$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6800			5.75	
$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6802			4.46	
Gate to Drain Charge	Q_{gd}			
$V_{GS} = 10\text{ V}, I_D = 8.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6796			16.59	nC
$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6798			28.11	
$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}, V_{DS} = 50\text{ V}$ 2N6800			16.59	
$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}, V_{DS} = 50\text{ V}$ 2N6802			28.11	

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-on delay time	$t_{d(on)}$			
$I_D = 8.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 30\text{ V}$ 2N6796				ns
$I_D = 5.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 77\text{ V}$ 2N6798			30	
$I_D = 3.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 176\text{ V}$ 2N6800				
$I_D = 2.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 225\text{ V}$ 2N6802				
Rinse time	t_r			
$I_D = 8.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 30\text{ V}$ 2N6796			75	ns
$I_D = 5.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 77\text{ V}$ 2N6798			50	
$I_D = 3.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 176\text{ V}$ 2N6800			35	
$I_D = 2.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 225\text{ V}$ 2N6802			30	
Turn-off delay time	$t_{d(off)}$			
$I_D = 8.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 30\text{ V}$ 2N6796			40	ns
$I_D = 5.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 77\text{ V}$ 2N6798			50	
$I_D = 3.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 176\text{ V}$ 2N6800			55	
$I_D = 2.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 225\text{ V}$ 2N6802			55	
Fall time	t_f			
$I_D = 8.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 30\text{ V}$ 2N6796			45	ns
$I_D = 5.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 77\text{ V}$ 2N6798			40	
$I_D = 3.0\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 176\text{ V}$ 2N6800			35	
$I_D = 2.5\text{ A}, V_{GS} = +10\text{ V}, R_G = 7.5\text{ }\Omega, V_{DD} = 225\text{ V}$ 2N6802			30	
Diode Reverse Recovery Time	t_{rr}			
$di/dt \leq 100\text{ A}/\mu\text{s}, V_{DD} \leq 50\text{ V}, I_F = 8.0\text{ A}$ 2N6796			300	ns
$di/dt \leq 100\text{ A}/\mu\text{s}, V_{DD} \leq 50\text{ V}, I_F = 5.5\text{ A}$ 2N6798			500	
$di/dt \leq 100\text{ A}/\mu\text{s}, V_{DD} \leq 50\text{ V}, I_F = 3.0\text{ A}$ 2N6800			700	
$di/dt \leq 100\text{ A}/\mu\text{s}, V_{DD} \leq 50\text{ V}, I_F = 2.5\text{ A}$ 2N6802			900	

GRAPHS

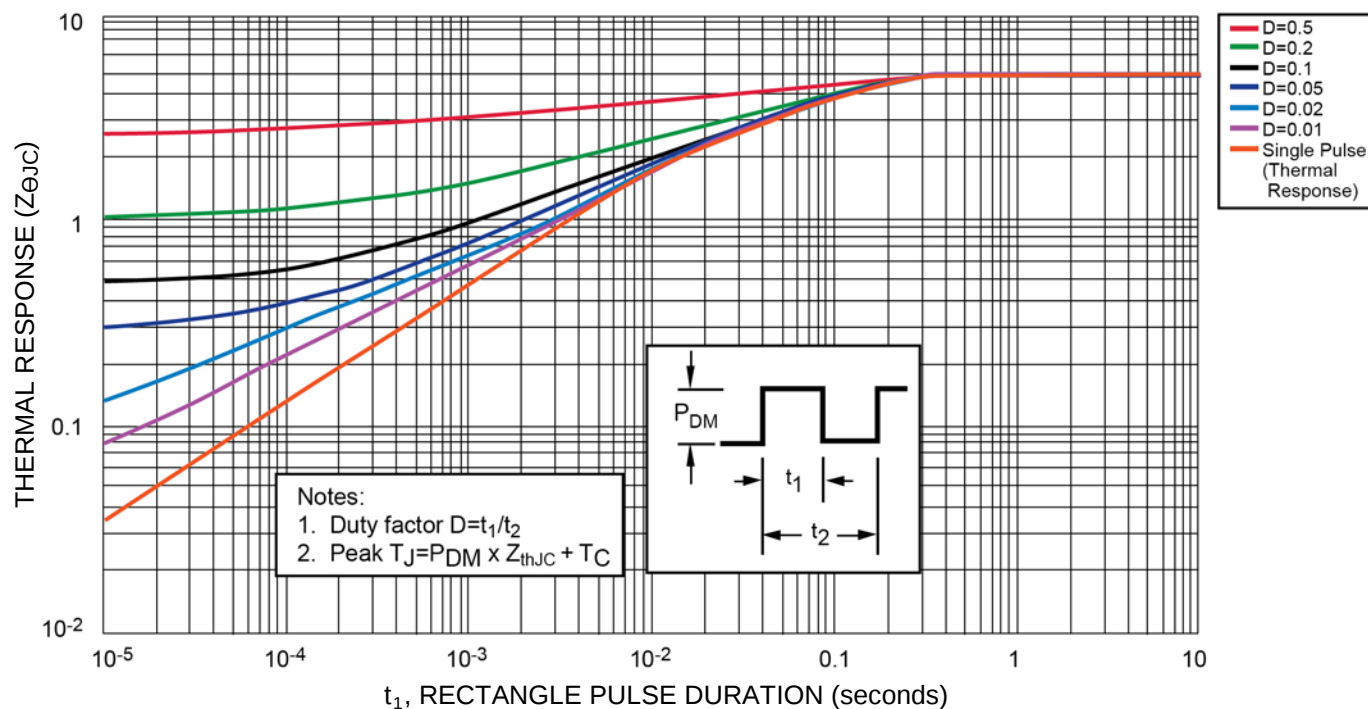
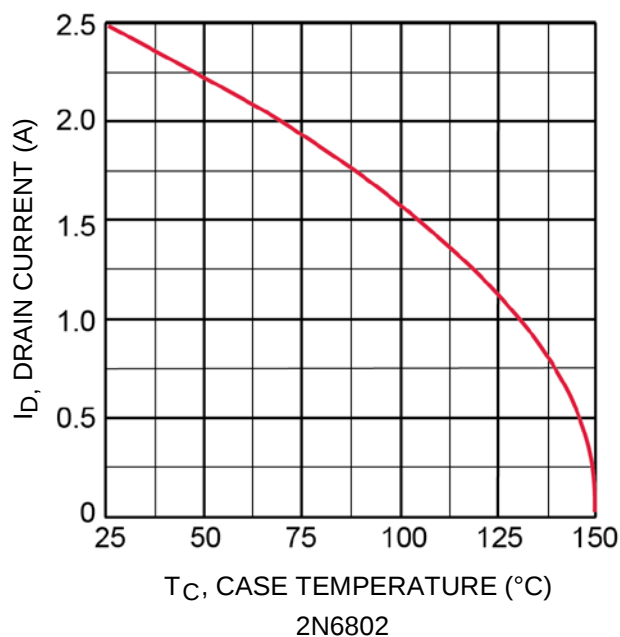
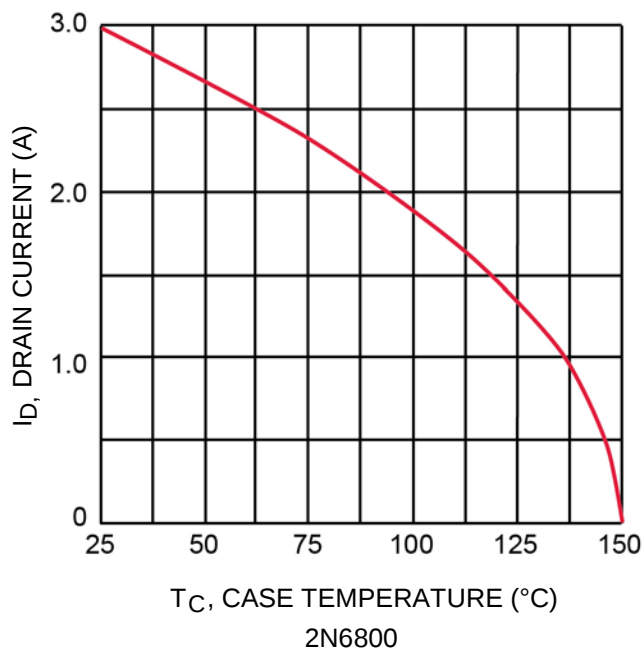
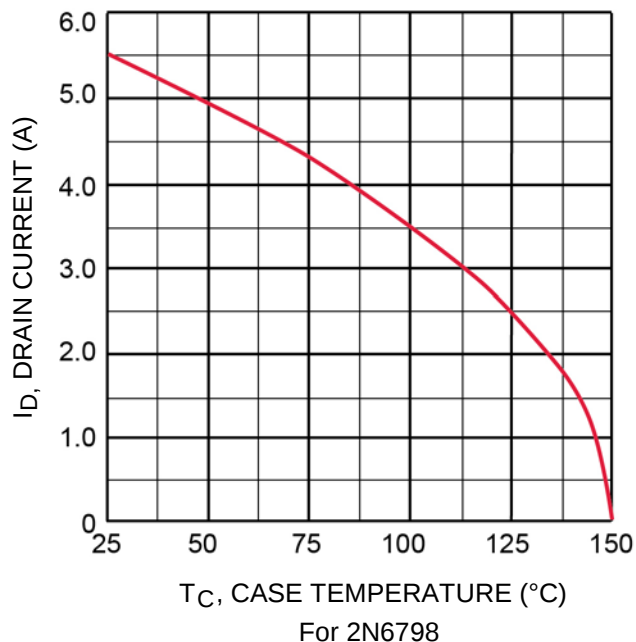
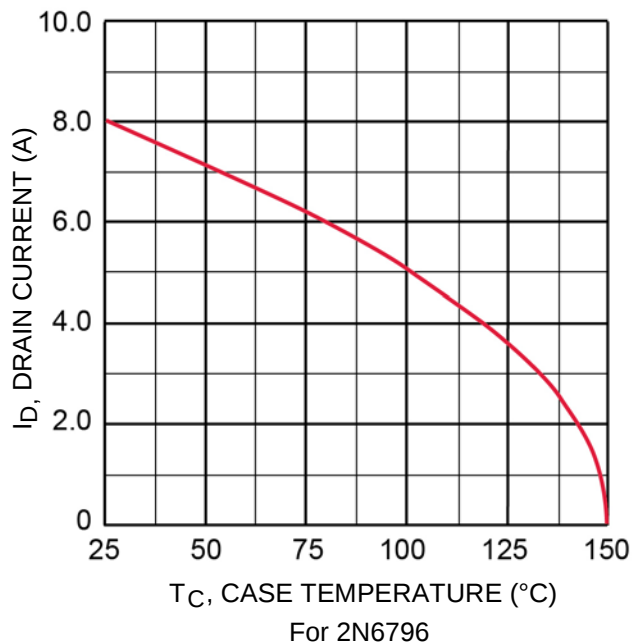
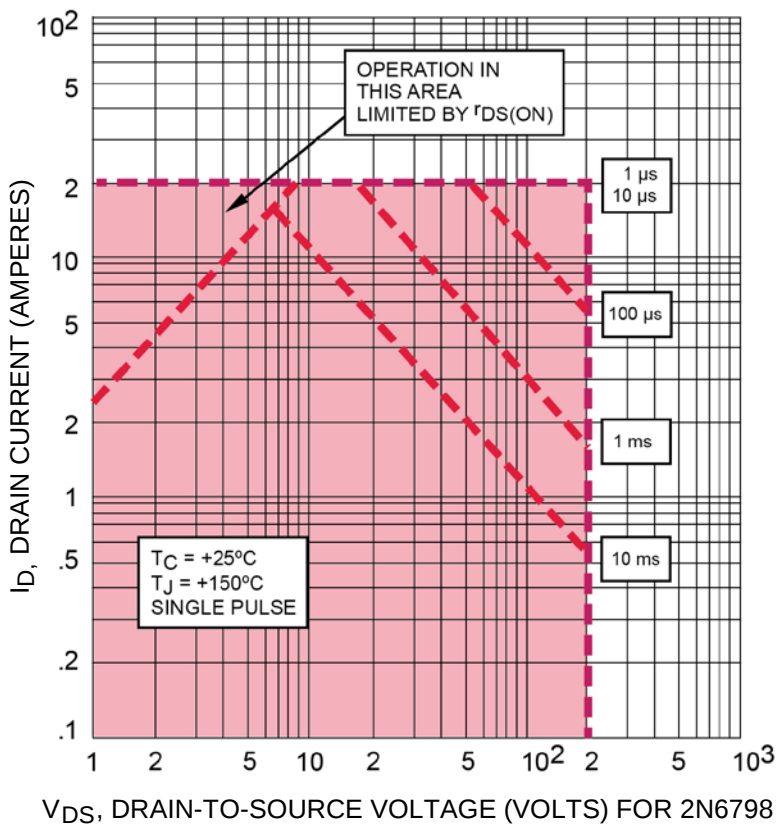
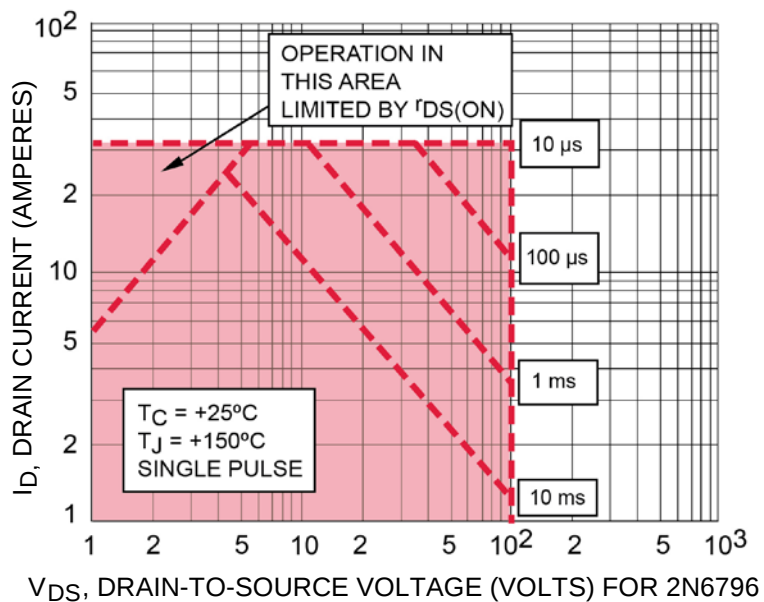


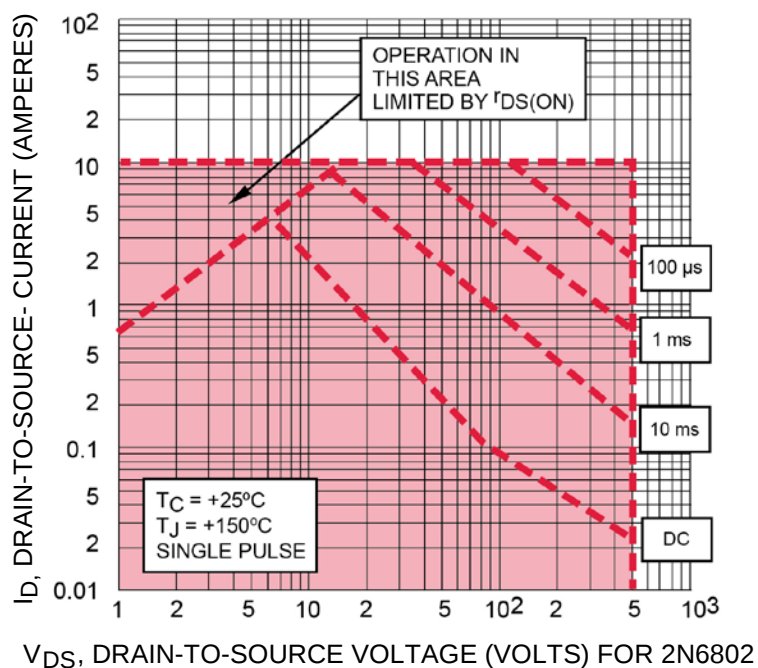
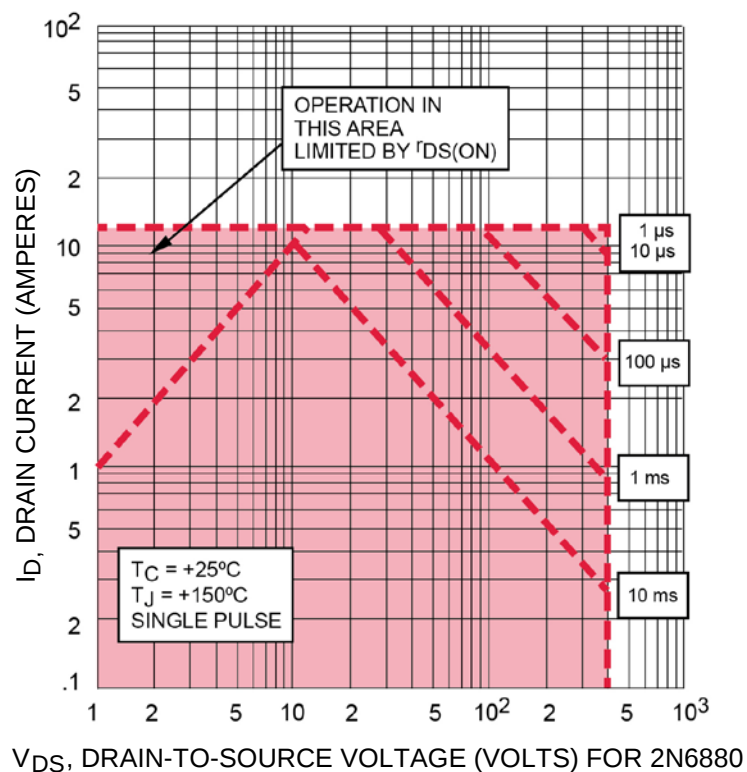
FIGURE 1 – Normalized Transient Thermal Impedance

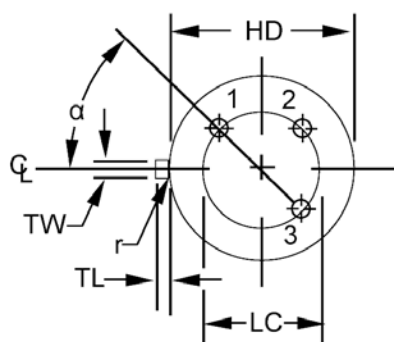
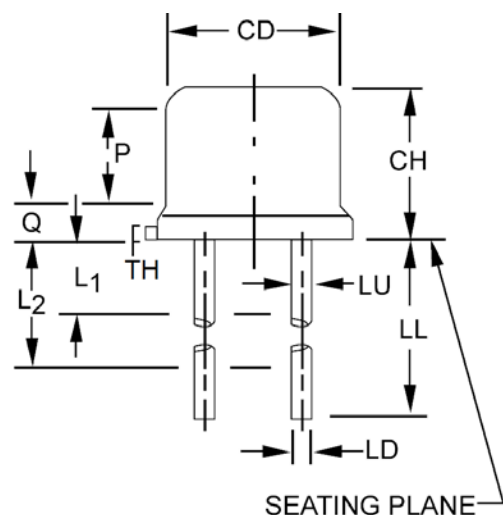
GRAPHS (continued)
FIGURE 2 – Maximum Drain Current versus Case Temperature Graphs


GRAPHS (continued)
FIGURE 3 – Maximum Safe Operating Area


GRAPHS (continued)

FIGURE 3 – Maximum Safe Operating Area (continued)



PACKAGE DIMENSIONS


Symbol	Dimensions				Note
	Inch		Millimeters		
	Min	Max	Min	Max	
CD	0.305	0.355	7.75	9.02	
CH	0.160	.180	4.07	4.57	
HD	0.335	0.370	8.51	9.39	
LC	0.200 TP		5.08 TP		6
LD	0.016	0.021	0.41	0.53	7, 8
LL	0.500	0.750	12.70	19.05	7, 8
LU	0.016	0.019	0.41	0.48	7, 8
L1		0.050		1.27	7, 8
L2	0.250		6.35		7, 8
P	.070		1.78		5
Q		0.050		1.27	4
TL	0.029	0.045	0.74	1.14	3
TW	0.028	0.034	0.72	0.86	2
TH	.009	.041	0.23	1.04	
r		0.010		0.25	9
α	45° TP		45° TP		6

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Beyond radius (r) maximum, j shall be held for a minimum length of .011 (0.028 mm).
3. Dimension TL measured from maximum HD.
4. Outline in this zone is not controlled.
5. Dimension CD shall not vary more than .010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
6. Leads at gauge plane .054 +.001, -.000 (1.37 +0.03, -0.00 mm) below seating plane shall be within .007 (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. LU applies between L1 and L2. LD applies between L2 and L minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
8. All three leads.
9. Radius (r) applies to both inside corners of tab.
10. Drain is electrically connected to the case.
11. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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